



BC857CQ

45V PNP SMALL SIGNAL TRANSISTOR IN SOT23

Description

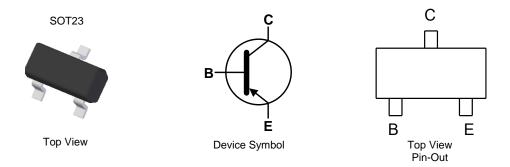
This Bipolar Junction Transistors (BJT) are designed to meet the stringent requirements of Automotive Applications.

Features

- Ideally Suited for Automatic Insertion
- Complementary NPN Types: BC847CQ
- For Switching and AF Amplifier Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208⁽²⁾
- Weight: 0.008 grams (Approximate)



Ordering Information (Note 5)

Part Number	Compliance	Marking	Reel Size (inches)	Quantity per Reel
BC857CQ-7-F	Automotive	K3G	7	3,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

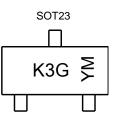
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/product-compliance-definitions/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



K3G = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: E = 2017) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Notes:

Year	2017	20	018	2019	2	2020	2021		2022	2023		2024
Code	E		F	G		Н			J	K		L
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Continuous Collector Current	I _C	-100	mA
Peak Collector Current	I _{CM}	-200	mA
Peak Emitter Current	I _{EM}	-200	mA
Peak Base Current	I _{BM}	-200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)	Р	310	mW	
	(Note 7)	- P _D	350	TITA	
Thermal Decistories, Junction to Ambient	(Note 6)	D	403	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	R _{0JA}	357	°C/W	
Thermal Resistance, Junction to Leads	(Note 8)	R _{θJL}	350	°C/W	
Operating and Storage Temperature Range	T _{J,} T _{STG}	-65 to +150	°C		

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

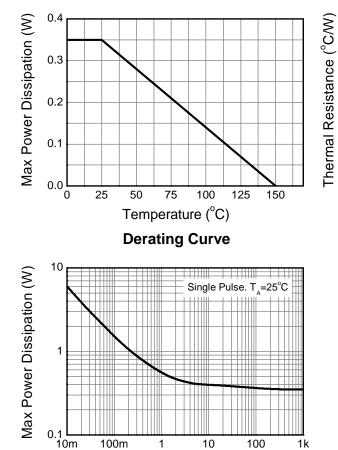
Notes: 6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

7. Same as Note 6, except the device is mounted on 15mm x 15mm 1oz copper.

Barrow Comparison of the device is mounted of romma forming to any 102 control of the leads).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information



100m

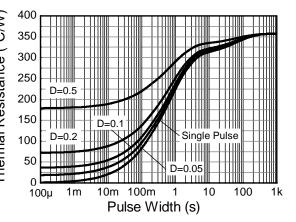
1

10

Pulse Width (s) **Pulse Power Dissipation**

100

1k







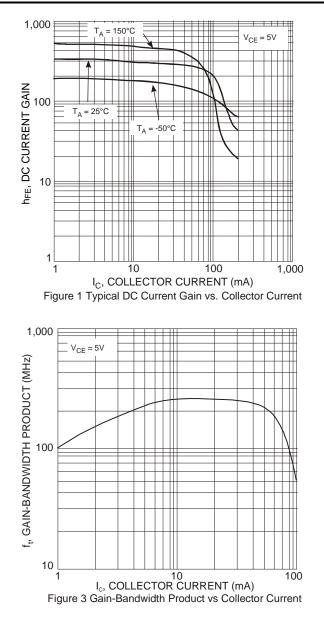
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

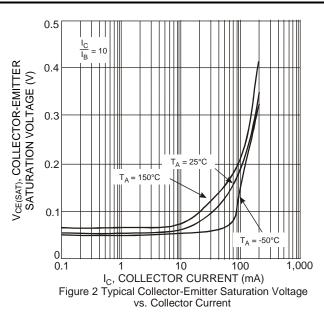
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BVCBO	-50	_	_	V	I _C = -10μΑ
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-45	—	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	—		V	$I_E = -1\mu A$
Collector Cutoff Current				-15	nA	V _{CB} = -30V
	ICBO			-4	μA	$V_{CB} = -30V, T_{J} = +150^{\circ}C$
Collector Emitter Cutoff Current	ICES	_	—	-15	nA	V _{CE} = -50V
Emitter-Base Cutoff Current	I _{EBO}	—	—	-100	nA	$V_{EB} = -5V$
Small Signal Current Gain (Note 10)	h _{fe}	—	600			
Input Impedance (Note 10)	h _{ie}	_	8.7	_	kΩ	I _C = -2.0mA, V _{CE} = -5V
Output Admittance (Note 10)	h _{oe}	—	60		μS	f = 1.0 kHz
Reverse Voltage Transfer Ratio (Note 10)	h _{re}	—	3x10 ⁻⁴	_	_	
DC Current Gain (Note 10)	h _{FE}	420	520	800	_	$I_{C} = -2.0 \text{mA}, V_{CE} = -5 \text{V}$
Collector-Emitter Saturation Voltage (Note 10)	Variation	_	-75	-300	mV	$I_{C} = -10 \text{mA}, I_{B} = -0.5 \text{mA}$
Collector-Emiller Saturation Voltage (Note 10)	V _{CE(SAT)}		-250	-650	IIIV	$I_{C} = -100 \text{mA}, I_{B} = -5.0 \text{mA}$
Base-Emitter Turn-On Voltage (Note 10)	V	-600	-650	-750	mV	$I_{C} = -2mA, V_{CE} = -5V$
	V _{BE(ON)}	_	—	-820	IIIV	$I_{C} = -10 \text{mA}, V_{CE} = -5 \text{V}$
Base-Emitter Saturation Voltage (Note 10)	V	_	-700	_	mV	$I_{C} = -10mA$, $I_{B} = -0.5mA$
Dase-Emilier Saldraion Voltage (Note 10)	V _{BE(SAT)}		-850	-1100		$I_{C} = -100 \text{mA}, I_{B} = -5 \text{mA}$
Output Capacitance	Сово	_	3	_	pF	$V_{CB} = -10V, f = 1.0MHz$
Transition Frequency	f⊤	100	200		MHz	$V_{CE} = -5V, I_C = -10mA, f = 100MHz$
Noise Figure	NF	_	2	10	dB	$\label{eq:Vce} \begin{split} V_{CE} &= \text{-5V}, \ I_C = \text{-200} \mu A \\ R_S &= 2 k \Omega, \ f = 1 k H z \\ \Delta f &= 200 H z \end{split}$

Note: 10. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





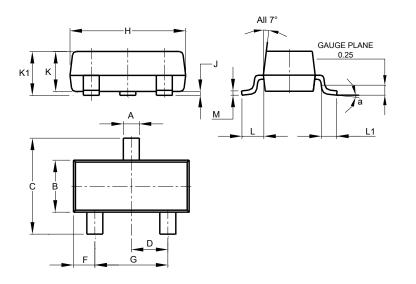


BC857CQ

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

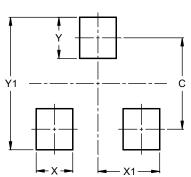
SOT23



	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
в	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
К	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
Μ	0.085	0.150	0.110				
а	0°	8°					
All	Dimens	ions in	mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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